

Silicon PNP Power Transistors

2SB1194

DESCRIPTION

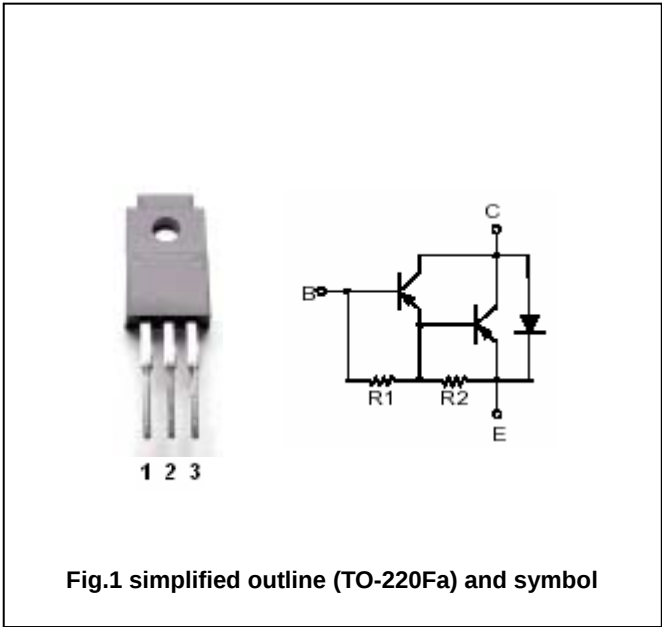
- With TO-220Fa package
- High DC current gain
- High speed switching
- DARLINGTON
- Complement to type 2SD1633

APPLICATIONS

- For power switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-100	V
V _{CEO}	Collector -emitter voltage	Open base	-100	V
V _{EBO}	Emitter-base voltage	Open collector	-7	V
I _C	Collector current		-5	A
I _{CM}	Collector current-peak		-8	A
I _B	Base current		-0.5	A
P _C	Collector power dissipation	T _a =25	2	W
		T _C =25	30	
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	$I_C = -0.2A$; $R_{BE} = \infty$	-100			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C = -3A$; $I_B = -3mA$			-1.5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C = -3A$; $I_B = -3mA$			-2.0	V
I_{CBO}	Collector cut-off current	$V_{CB} = -100V$; $I_E = 0$			-100	μA
I_{CEO}	Collector cut-off current	$V_{CE} = -100V$; $I_B = 0$			-100	μA
I_{EBO}	Emitter cut-off current	$V_{EB} = -7V$; $I_C = 0$			-5	mA
h_{FE}	DC current gain	$I_C = -3A$; $V_{CE} = -3V$	1500		10000	

Switching times

t_{on}	Turn-on time	$I_C = -3A$; $I_{B1} = -I_{B2} = -3mA$ $V_{CC} = -50V$			3.0	μs
t_{stg}	Storage time				5.0	μs
t_f	Fall time				3.0	μs

◆ h_{FE} Classifications

Q	P
1500-6000	4000-10000

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PACKAGE OUTLINE

